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1SS383T1G

Preferred Device

Dual Schottky Diode

Dual 40 V, 300 mA Low $V_{\rm F}$ Schottky Diodes in 4–lead SC–82 package.

Features

- Low Forward Voltage: $V_F = 0.48 \text{ V} (\text{typ}) @ I_F = 100 \text{ mA}$
- Low Reverse Current: $I_R = 5 \mu A (max)$
- This is a Pb–Free Device*

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Continuous Reverse Voltage	V _R	40	V
Maximum Peak Forward Current*	I _{FM}	300	mA
Peak Forward Surge Current Pulse Width = 10 μ s	I _{FM(surge)}	500	mA

THERMAL CHARACTERISTICS

Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P _D	200 (Note 1) 1.6 (Note 1)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	625 (Note 1)	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. *Both Devices Active

1. FR-4 @ Minimum Pad.

Characteristic Symbol Min Max Unit Тур Forward Voltage V_{F} mV 280 $(I_{F} = 1.0 \text{ mA})$ _ 360 _ $(I_{F} = 10 \text{ mA})$ _ 540 600 $(I_{F} = 100 \text{ mA})$ μΑ **Reverse Current** I_R (V_R = 40 V) 5 _ _ Capacitance C_D pF 25 $(V_R = 0, f = 1.0 \text{ MHz})$ _

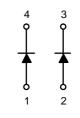
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

http://onsemi.com





SC-82 CASE 900AA

MARKING DIAGRAM



AE = Specific Device Code M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
1SS383T1G	SC-82 (Pb-Free)	3000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

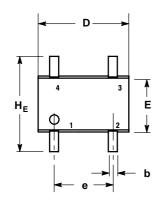
Preferred devices are recommended choices for future use and best overall value.

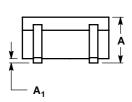
1SS383T1G

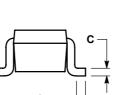
PACKAGE DIMENSIONS

SC-82, 4 LEAD, GULL WING

CASE 900AA-01 ISSUE O







NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
- 2 CONTROLLING DIMENSION: MILLIMETERS 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS
- THE MINIMUMTHICKNESS OF BASE MATERIAL DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.90	1.00	0.032	0.035	0.04	
A 1	0		0.10	0		0.004	
b	0.10	0.20	0.30	0.004	0.008	0.012	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.00	2.20	0.071	0.079	0.087	
Е	1.15	1.25	1.35	0.045	0.049	0.053	
е	1.30 BSC		0.051 BSC				
ΗE	2.00	2.10	2.20	0.079	0.083	0.087	
L	0.10	0.20	0.30	0.004	0.008	0.012	

STYLE 1: PIN 1. ANODE 1 2. ANODE 2 3. CATHODE 2 4. CATHODE 1

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